DC–30000 MHz 3 dB GaAs IPD fixed attenuator die

LCATT-DC-30000-A3-S0p35X0p35 — DC–30000 MHz 3 dB GaAs IPD fixed attenuator die.

Attenuation: 3 dB; Input/output VSWR: 1.3 ; Attenuation flatness: ±0.4 dB. Die dimensions: 0.35 × 0.35 × 0.1 mm.



RF characteristics

TA = +25 °C

Parameter	Symbol	Minimum	Typical	Maximum	Value	Unit
Operating frequency	-	0	-	30000	DC–30000	MHz
Attenuation	-	-	-	-	3	dB
Input/output VSWR	-	-	-	-	1.3	-
Attenuation flatness	-	-	-	-	±0.4	dB

Absolute limits

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Maximum input power	-	-	-	30	dBm

Environmental specifications

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Storage temperature	-	-65	-	150	°C
Operating temperature	-	-55	-	125	°C

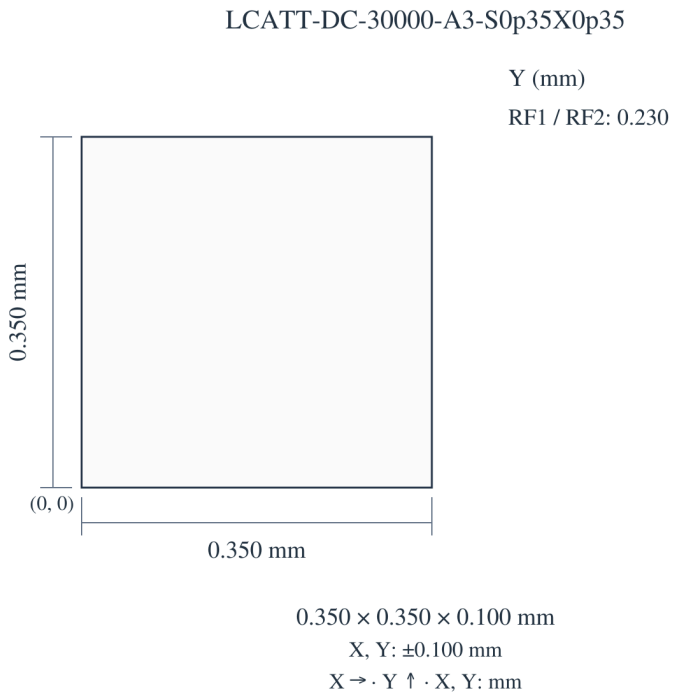
Bond-pad assignments

Pins	Symbol	mm
1	GND	0.100 × 0.050
2	RF1	0.132 × 0.087
3	RF2	0.132 × 0.087
4	GND	0.100 × 0.050

Die dimensions

Parameter	Value	Unit
Die dimensions	0.35 × 0.35 × 0.1	mm

Outline and dimensioned coordinates in mm. Use this drawing as a dimensional reference. Fabrication and wire bonding require complete drawings.



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Die integration and bias sequencing

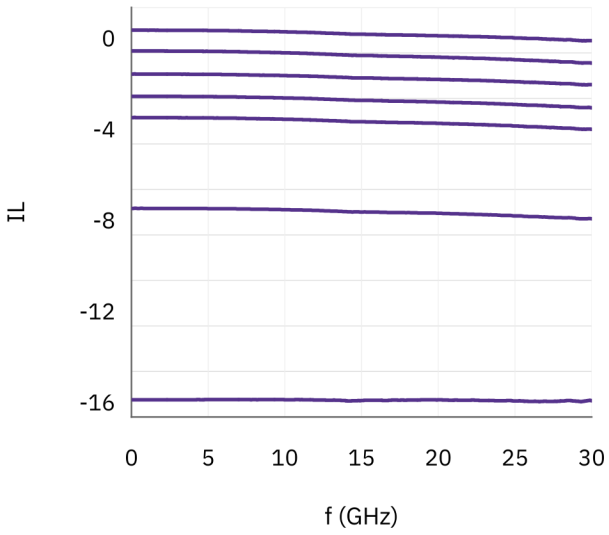
The die backside requires a reliable ground connection.

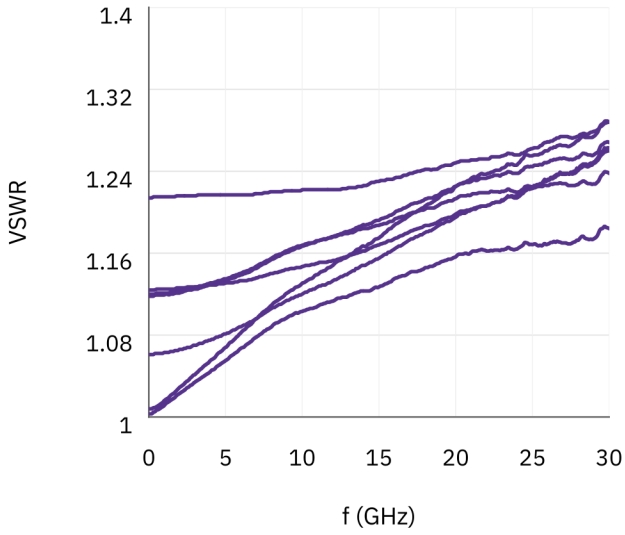
Performance curves

Read each figure with its stated operating conditions.

Series reference curves — Port matching; Insertion loss.

Figure notes: TA=+25°C. Readings are approximate. These curves provide a common reference for 7 models in the series. Individual traces are not model-specific. The IL axis has no specified unit.





Document notice

Specifications are subject to revision. Before design release, confirm the current document revision and product-specific requirements with LCRF. The approved quotation and order documentation define the supplied configuration.